

IN THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A process of forming a metallization comprising:
forming a first interlayer dielectric (ILD) layer above a substrate;
forming a first recess in the first ILD layer;
filling the first recess with a first interconnect;
forming a conductive first diffusion barrier layer above and on the first interconnect;
forming an upper ILD layer above the first conductive diffusion barrier layer;
forming an upper recess in the upper ILD layer to optionally expose the first conductive diffusion barrier layer;
forming an upper interconnect in the upper recess; and
forming a conductive upper diffusion barrier layer above and on the upper interconnect.
2. (Previously Presented) A process of forming a metallization comprising:
forming a first interlayer dielectric (ILD) layer above a substrate;
forming a first recess in the first ILD layer;
filling the first recess with a first interconnect;
forming a conductive first diffusion barrier layer above and on the first interconnect;
forming an upper ILD layer above the first conductive diffusion barrier layer;
forming an upper recess in the upper ILD layer to expose the first conductive diffusion barrier layer;
forming an upper interconnect in the upper recess; and
forming a conductive upper diffusion barrier layer above and on the upper interconnect, wherein at least one of forming a conductive first diffusion barrier layer and forming a conductive upper diffusion barrier layer includes:
electroless plating the conductive diffusion barrier layer.
3. (Original) The process according to claim 1, wherein at least one of forming a conductive first diffusion barrier layer and forming a conductive upper diffusion barrier layer includes:

vapor depositing the conductive diffusion barrier layer, selected from chemical vapor deposition, plasma-enhanced chemical vapor deposition, atomic layer chemical vapor deposition, and physical vapor deposition.

4. (Original) The process according to claim 1, further including:
forming a barrier film in at least one of the first recess and the upper recess; and
optionally forming a conductive seed film over the barrier film.
5. (Previously Presented) The process according to claim 1, further including:
forming a barrier film in at least one of the first recess and the upper recess;
forming a conductive diffusion barrier film over at least one of the barrier films; and
optionally forming a conductive seed film over the conductive diffusion barrier film.
6. (Original) The process according to claim 1, wherein forming a first ILD layer includes forming an organic ILD layer, further including:
forming a hard mask above and on the organic ILD layer; and
patterning an opening in the hard mask.
7. (Original) The process according to claim 1, further including:
forming a first hard mask above and on the first ILD layer;
patterning an opening in the first hard mask;
forming an upper hard mask above and on the upper ILD layer;
patterning an opening in the upper hard mask.
8. (Original) The process according to claim 1, wherein forming a first ILD layer includes:
forming an inorganic first bottom ILD layer; and
forming an organic first top ILD layer.
9. (Original) The process according to claim 8, wherein forming a first recess includes:

forming a dual-damascene recess in the inorganic first bottom ILD layer and in the organic first top ILD layer.

10. (Original) The process according to claim 9, further including:
forming a first hard mask above and on the organic first top ILD layer; and
patterning an opening in the first hard mask.
11. (Currently amended) A process of forming a metallization comprising:
forming a first interlayer dielectric (ILD) layer above a substrate;
forming a first recess in the first ILD layer;
filling the first recess with a first interconnect;
forming a conductive first diffusion barrier layer above and [[an]] on the first interconnect;
forming an upper ILD layer above the first conductive diffusion barrier layer;
forming an upper recess in the upper ILD layer to optionally expose the first conductive diffusion barrier layer;
forming an upper interconnect in the upper recess; and
forming a conductive upper diffusion barrier layer above and on the upper interconnect, wherein forming an upper ILD layer includes:
forming an inorganic upper bottom ILD layer; and
forming an organic upper top ILD layer, and wherein forming an upper recess includes forming a dual-damascene recess in the inorganic upper bottom ILD layer and in the organic upper top ILD layer, wherein forming a first ILD layer includes:
forming an inorganic first bottom ILD layer; and
forming an organic first top ILD layer.
12. (Original) The process according to claim 11, further including:
forming an upper hard mask above and on the upper bottom ILD layer; and
patterning an opening in the upper hard mask.

13. (Original) The process according to claim 1, wherein forming a first ILD layer includes:

forming an organic first bottom ILD layer; and
forming an inorganic first top ILD layer.

14. (Original) The process according to claim 13, wherein forming a first recess includes:

forming a dual-damascene recess in the organic first bottom ILD layer and in the inorganic first top ILD layer.

15. (Original) The process according to claim 14, further including:

forming a first hard mask above and on the organic first bottom ILD layer; and
patterning an opening in the first hard mask.

16. (Original) The process according to claim 13, wherein forming an upper ILD layer includes:

forming an organic upper bottom ILD layer; and
forming an inorganic upper top ILD layer, and wherein forming an upper recess includes forming a dual -damascene recess in the organic upper bottom ILD layer and in the inorganic upper top ILD layer.

17. (Original) The process according to claim 16, further including:

forming an upper hard mask above and on the upper bottom ILD layer; and
patterning an opening in the upper hard mask.